

60V P-Channel MOSFETs

General Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDS(ON)	ID
-60V	8.6mΩ	-72A

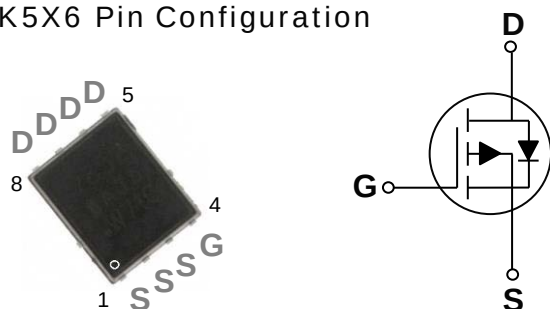
Features

- -60V, -72A, $R_{DS(ON)} = 8.6m\Omega @ V_{GS} = -10V$
- Fast switching
- Green Device Available
- Suit for -4.5V Gate Drive Applications

Applications

- POL Applications
- Load Switch
- LED Application

PPAK5X6 Pin Configuration



Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	-72	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	-45.5	A
I_{DM}	Drain Current – Pulsed ¹	-288	A
EAS	Single Pulse Avalanche Energy ²	320	mJ
IAS	Single Pulse Avalanche Current ²	80	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	142	W
	Power Dissipation – Derate above 25°C	1.13	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.88	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	---	62	$^\circ\text{C}/\text{W}$



FTK6901DFN56

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.036	---	V/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-60V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-48V$, $V_{GS}=0V$, $T_J=125^\circ\text{C}$	---	---	-10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V$, $I_D=-20A$	---	7.1	8.6	m Ω
		$V_{GS}=-4.5V$, $I_D=-10A$	---	8.8	12	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.2	-1.6	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-6.3	---	mV/ $^\circ\text{C}$
g_{fs}	Forward Transconductance	$V_{DS}=-10V$, $I_D=-3A$	---	18	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{3, 4}	$V_{DS}=-48V$, $V_{GS}=-10V$, $I_D=-5A$	---	141	210	nC
Q_{gs}	Gate-Source Charge ^{3, 4}		---	17	25.5	
Q_{gd}	Gate-Drain Charge ^{3, 4}		---	28.6	43	
$T_{d(on)}$	Turn-On Delay Time ^{3, 4}	$V_{DD}=-48V$, $V_{GS}=-10V$, $R_G=6\Omega$ $I_D=-1A$	---	70	140	ns
T_r	Rise Time ^{3, 4}		---	205	410	
$T_{d(off)}$	Turn-Off Delay Time ^{3, 4}		---	402	804	
T_f	Fall Time ^{3, 4}		---	197	394	
C_{iss}	Input Capacitance	$V_{DS}=-25V$, $V_{GS}=0V$, $F=1MHz$	---	8620	12930	pF
C_{oss}	Output Capacitance		---	486	730	
C_{rss}	Reverse Transfer Capacitance		---	288	430	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-72	A
I_{SM}	Pulsed Source Current		---	---	-144	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=50V$, $V_{GS}=10V$, $L=0.1mH$, $I_{AS}=80A$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$.
3. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

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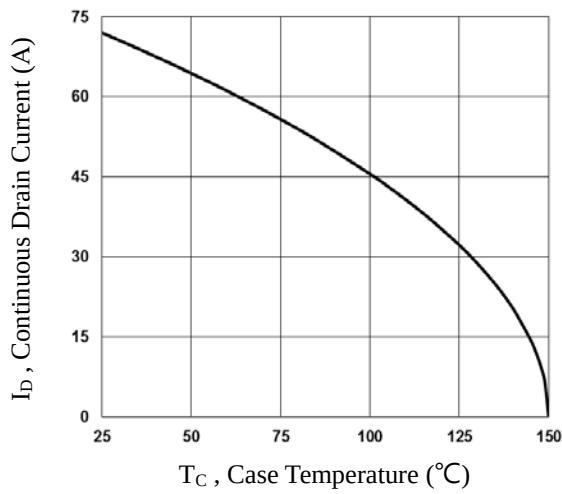


Fig.1 Continuous Drain Current vs. T_C

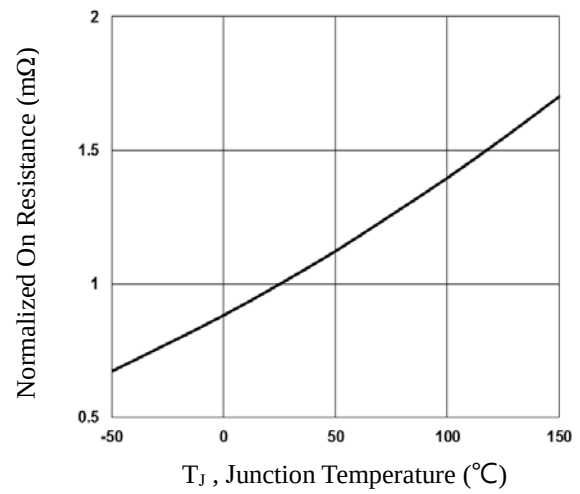


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

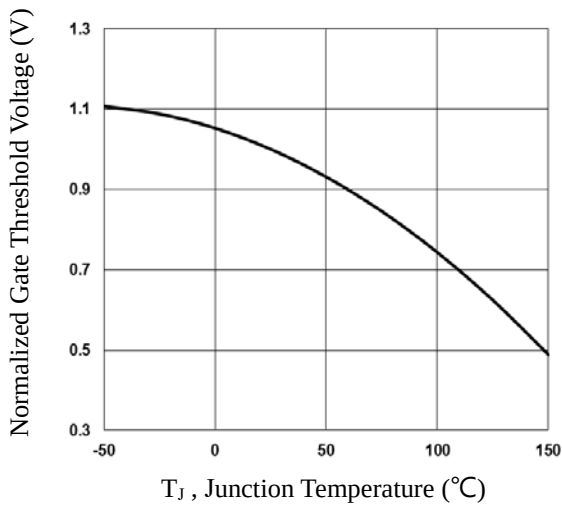


Fig.3 Normalized V_{th} vs. T_J

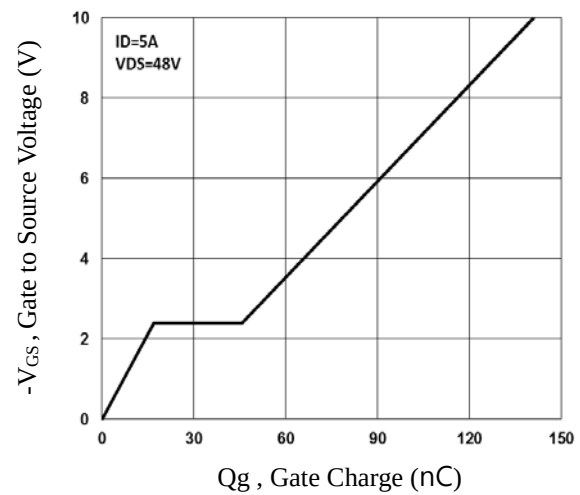


Fig.4 Gate Charge Waveform

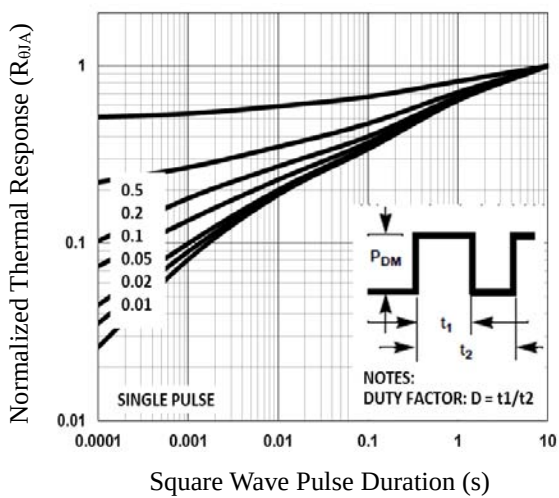


Fig.5 Normalized Transient Impedance

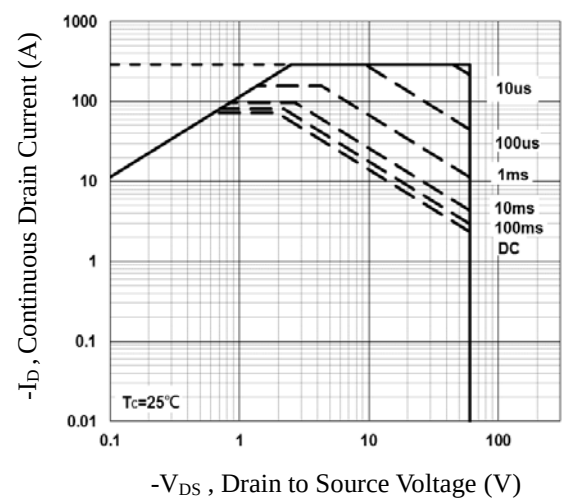


Fig.6 Maximum Safe Operation Area

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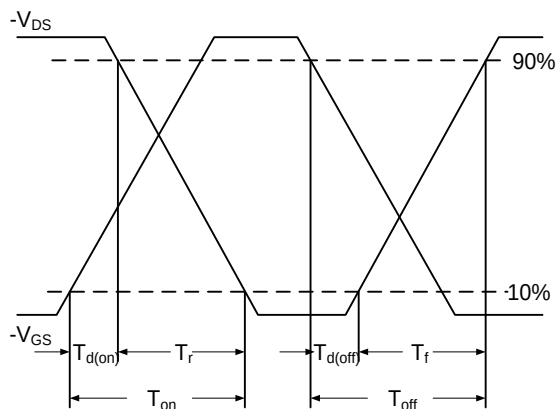


Fig.7 Switching Time Waveform

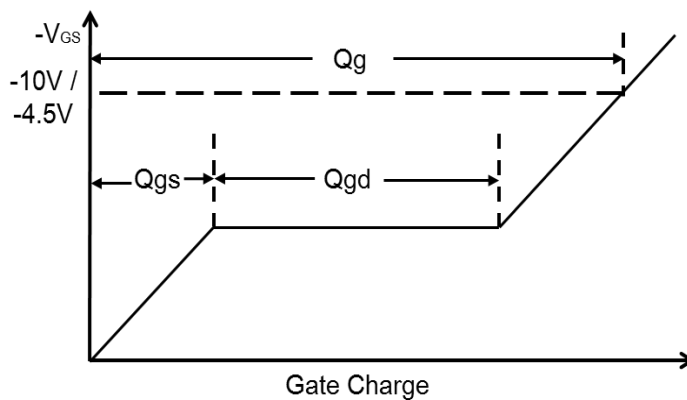
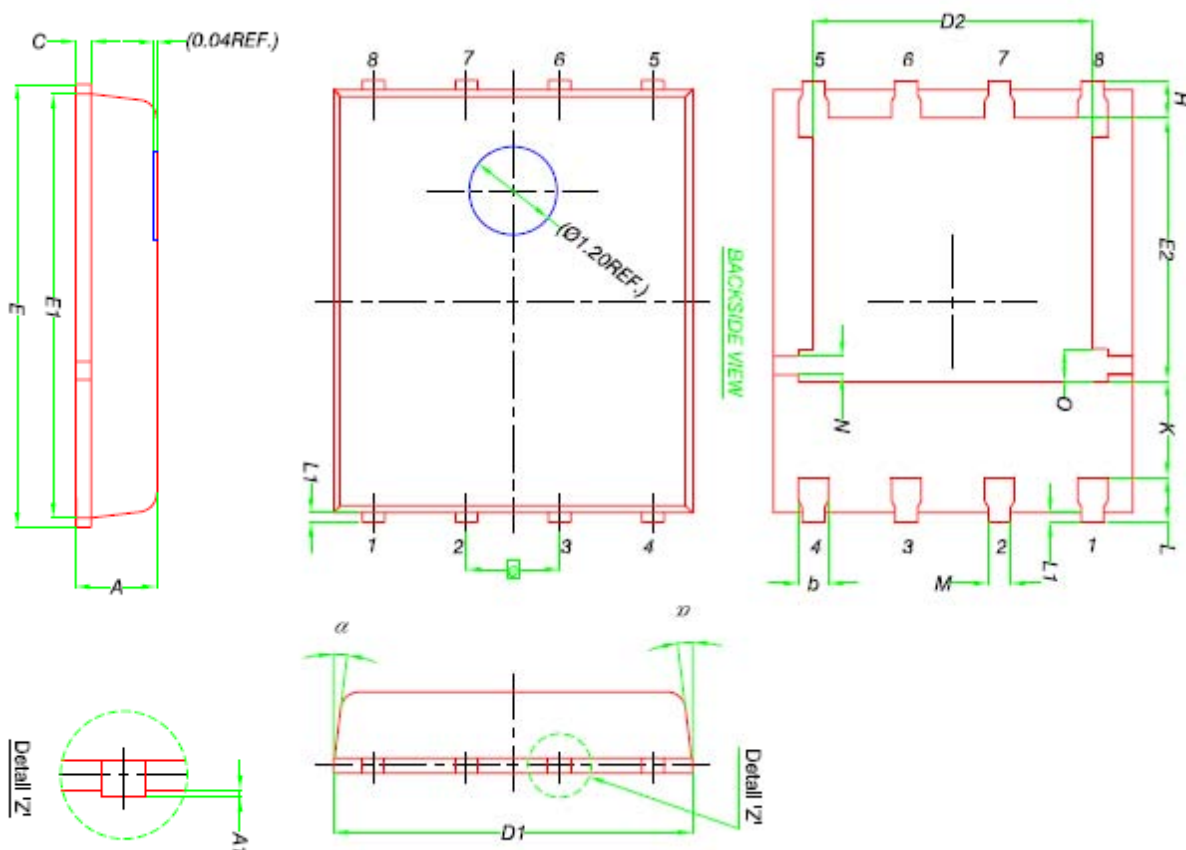


Fig.8 Gate Charge Waveform

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PPAK5X6 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters			Symbol	Dimensions In Millimeters		
	Min	Typ	Max		Min	Typ	Max
A	0.70	1.00	1.10	e	1.27BSC		
A1	0.00	---	0.05	H	0.41	0.51	0.61
b	0.33	0.41	0.51	K	1.1	-	-
C	0.20	0.25	0.30	L	0.51	0.61	0.71
D1	4.80	4.90	5.00	L1	0.06	0.13	0.2
D2	3.61	3.81	3.96	α	0°	-	12°
E	5.90	6.00	6.10	M	0.2	0.33	0.45
E1	5.70	5.75	5.80	N	0.18	0.25	0.35
E2	3.38	3.58	3.78	O	0.35	0.45	0.55

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Recommend Land Pattern

